

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
250V	18mΩ@10V	70A

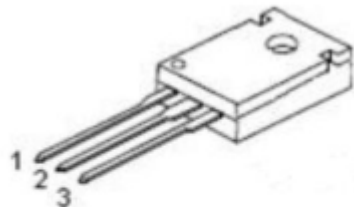
Feature

- Fast Switching
- Low Gate Charge and Rdson
- 100% Single Pulse avalanche energy Test

Application

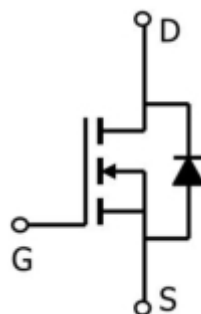
- Power switching application
- DC-DC Converter
- Power Management

Package

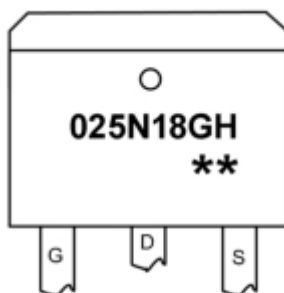


TO-247(1:G 2:D 3:S)

Circuit diagram



Marking



025N18GH : Product code
 ** : Week code

Absolute maximum ratings

(T_a=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain source voltage	V _{DS}	250	V
Gate source voltage	V _{GS}	±20	V
Continuous drain current(Tc=25°C)	I _D	70	A
Pulsed drain current	I _{DM}	280	A
Power dissipation(Tc=25°C)	P _D	390	W
Single pulsed avalanche energy ¹⁾	E _{AS}	972	mJ
Thermal resistance, junction-case	R _{θJC}	0.32	°C/W
Operation and storage temperature	T _J	-55 to 150	°C

Electrical characteristics

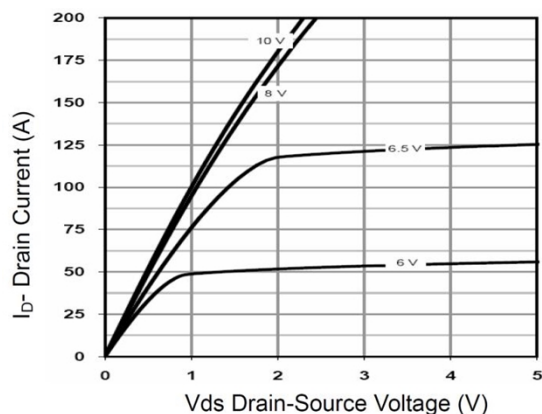
(T_A=25°C, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	BV (BR)DSS	V _{GS} = 0V, I _D =250μA	250			V
Drain Cut-Off Current	I _{DSS}	V _{DS} =200V,V _{GS} = 0V			1	uA
Gate-body leakage current	I _{GSS}	V _{GS} = ±20V , V _{DS} =0V			±0.1	uA
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	2.5	3.5	4.5	V
Drain-source on-resistance	R _{DS(on)}	V _{GS} =10V, I _D =30A		18	23	mΩ
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} =25V, V _{GS} =0V, f=1MHz		5500		pF
Output Capacitance	C _{OSS}			903		
Reverse Transfer Capacitance	C _{rss}			4.6		
Switching Characteristics						
Total Gate Charge	Q _g	V _{DS} =125V, V _{DS} =10V, I _D =40A		80		pF
Gate-Source Charge	Q _{gs}			28		
Gate-Drain Charge	Q _{gd}			26		
Turn-On Delay Time	T _{d(on)}	V _{GS} =10V, V _{DS} =125V, I _D =40A, R _G =5Ω		33		nS
Rise Time	T _r			15		
Turn-Off Delay Time	T _{d(off)}			61		
Fall Time	T _f			8		
Drain-Source Body Diode Characteristics						
Source-Drain Diode Forward Voltage	V _{SD}	V _{GS} =0V , I _S =1A			1.2	V

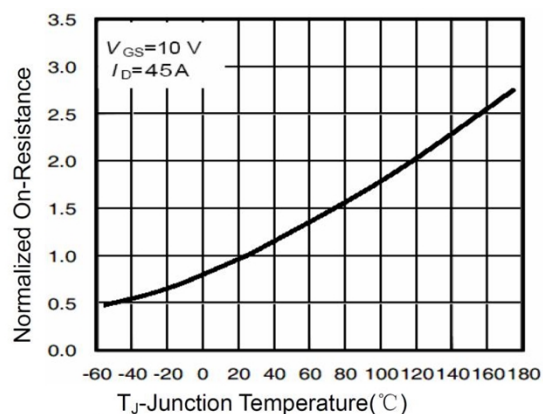
Note:

1. E_{AS} is tested at starting T_j = 25°C, V_{DD} = 75V, V_{GS} = 10V, L = 0.5mH, R_G = 25mΩ;

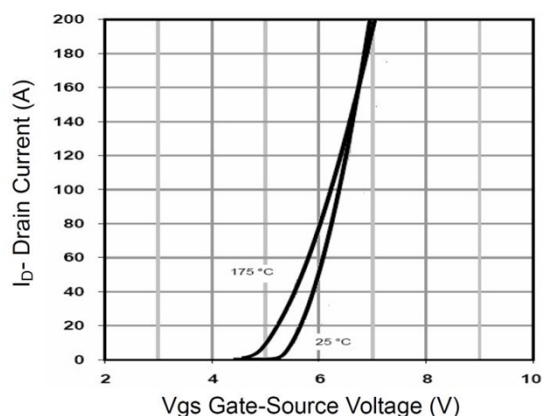
Typical Characteristics



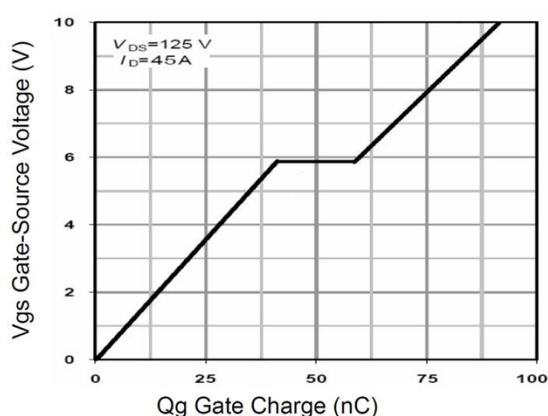
Output Characteristics



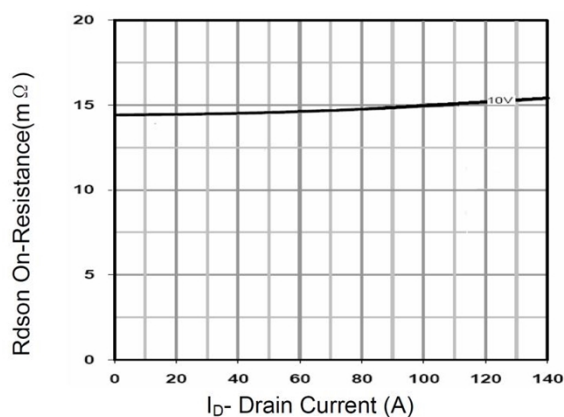
Rdson-Junction Temperature



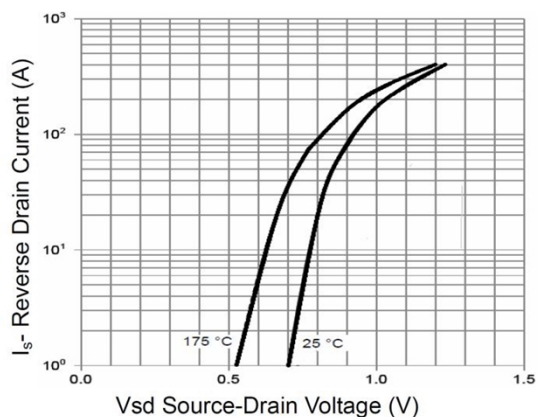
Transfer Characteristics



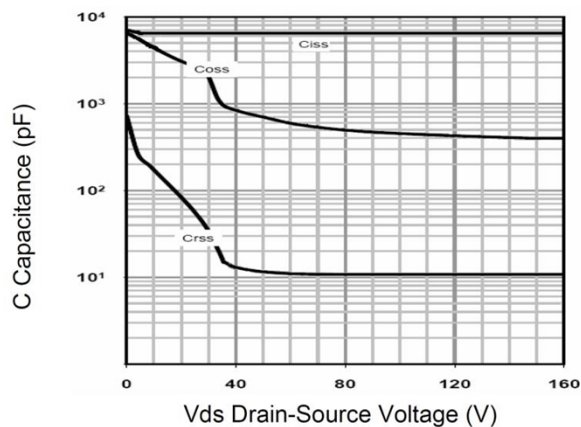
Gate Charge



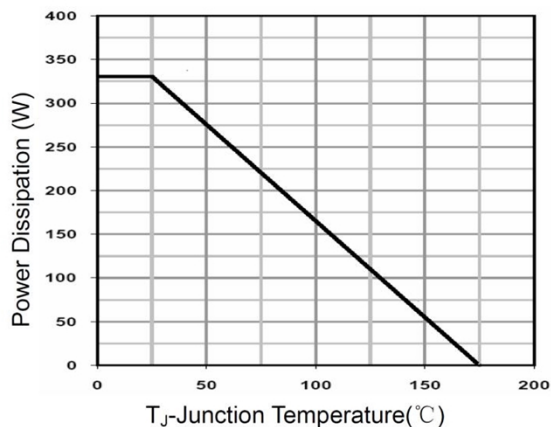
Rdson- Drain Current



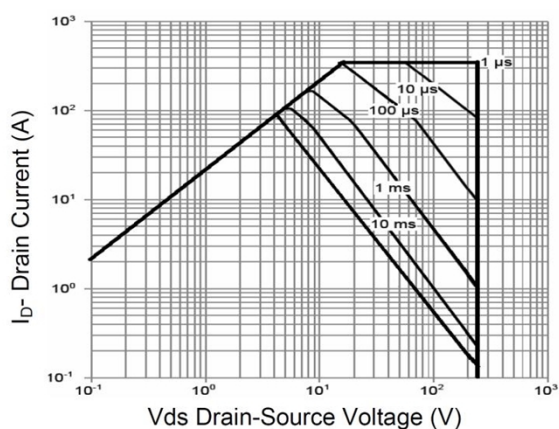
Source- Drain Diode Forward



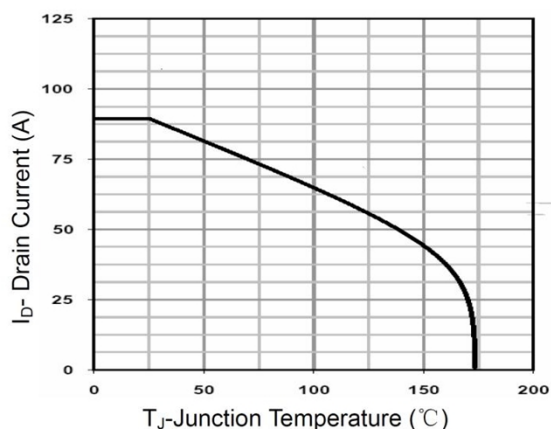
Capacitance vs Vds



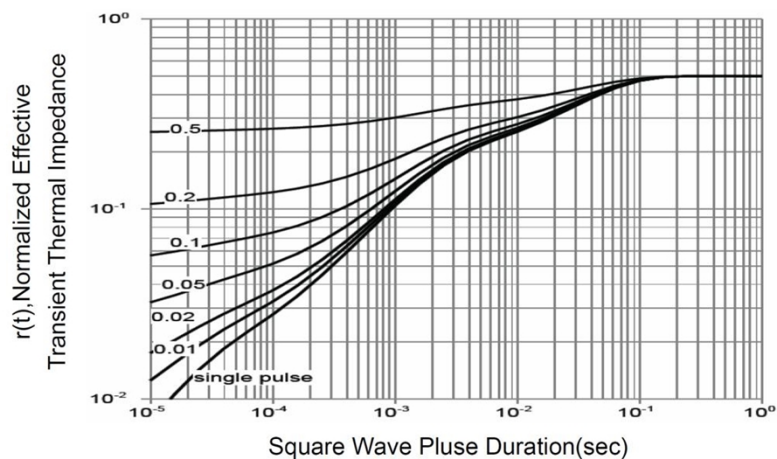
Power De-rating



Safe Operation Area

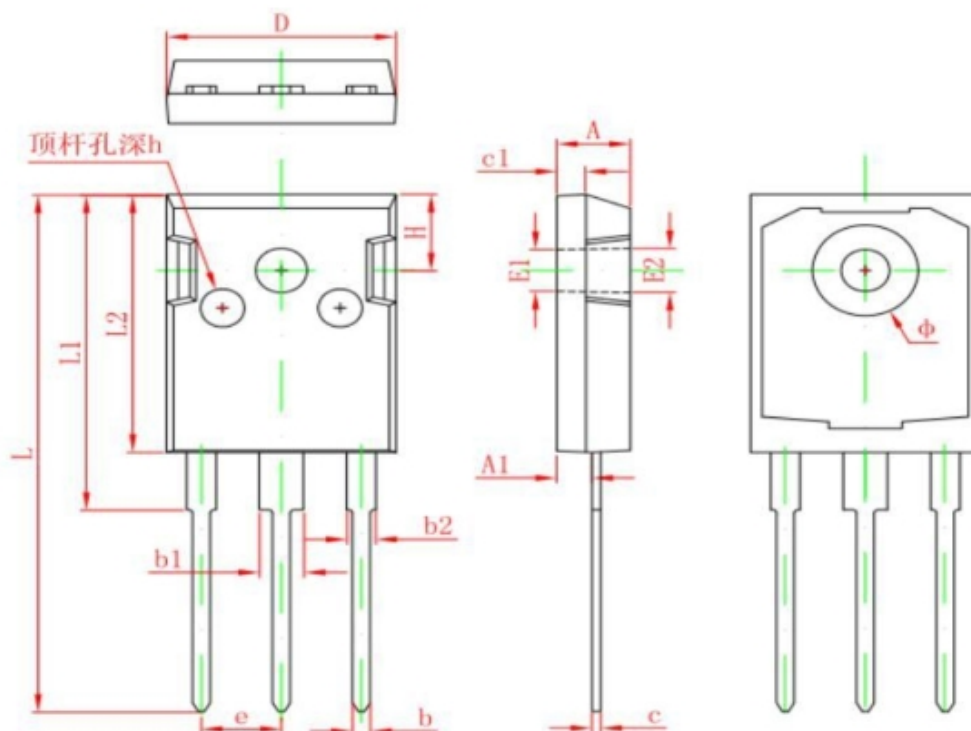


Current De-rating



Normalized Maximum Transient Thermal Impedance

TO-247 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.850	5.150	0.191	0.200
A1	2.200	2.600	0.087	0.102
b	1.000	1.400	0.039	0.055
b1	2.800	3.200	0.110	0.126
b2	1.800	2.200	0.071	0.087
c	0.500	0.700	0.020	0.028
c1	1.900	2.100	0.075	0.083
D	15.450	15.750	0.608	0.620
E1	3.500 REF.		0.138 REF.	
E2	3.600 REF.		0.142 REF.	
L	40.900	41.300	1.610	1.626
L1	24.800	25.100	0.976	0.988
L2	20.300	20.600	0.799	0.811
Φ	7.100	7.300	0.280	0.287
e	5.450 TYP.		0.215 TYP.	
H	5.980 REF.		0.235 REF.	
h	0.000	0.300	0.000	0.012